Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT428 (DPAK) surface-mountable plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Surface-mountable package
- · Triggering in all four quadrants

3. Applications

- · General purpose motor controls
- · General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	8	А
	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	65	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	-	71	Α
Tj	junction temperature		-	-	125	°C
Static charact	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	4	10	mA

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$		-	5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>		-	11	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>		-	2.5	20	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>		-	1.3	1.65	V
Dynamic cha	Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		-	50	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	А	anode		A
3	G	gate		G sym037
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

rabic o. Oracining ii			1	1		1
Type number	Package	Orderable part number	Packing	Small packing	Package	Package
	Name		method	quantity	version	issue date
BT137S-800E	TO252	BT137S-800E,118	Reel	2500	TO252N	07-Mar-2025
					TO252Q	05-Mar-2025

Type number	Marking codes	
	Assembly factory: N	Assembly factory: Q
BT137S-800E	137S8E PJNxxxx xx	137S8E PJQxxxx xx

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	8	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	65	Α
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	71	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	21	A²s
dl _T /dt	rate of rise of on-state current	I _G = 50 mA	-	50	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		_	125	°C

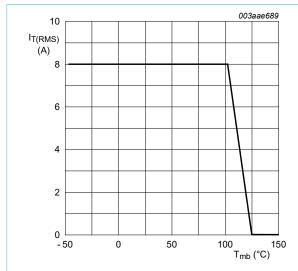


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

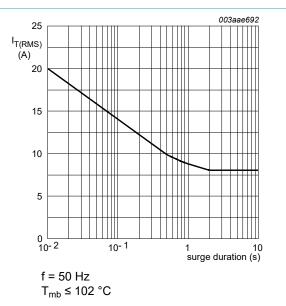


Fig. 2. RMS on-state current as a function of surge duration; maximum values

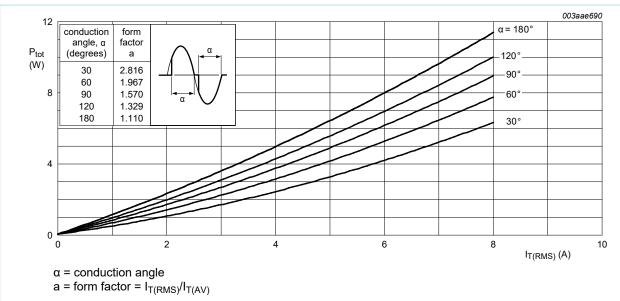


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

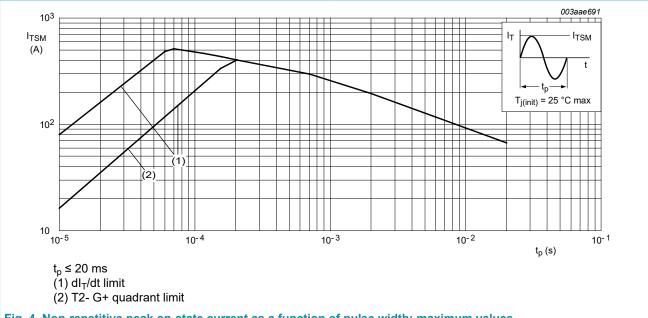


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
from junct	thermal resistance	half cycle; Fig. 6	-	-	2.4	K/W
	from junction to mounting base	full cycle; Fig. 6	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	PCB (FR4) mounted; minimum pad sizes	-	75	-	K/W

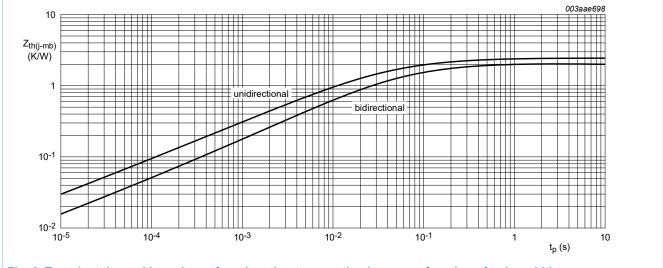
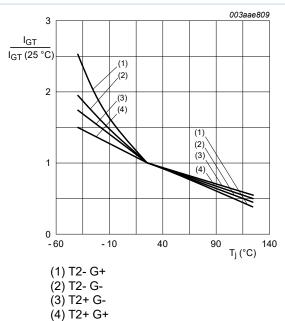


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

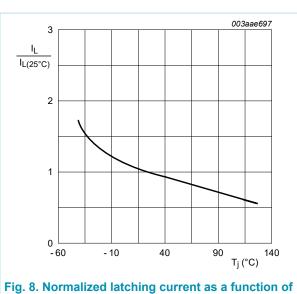
9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{G-;} $ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	5	10	mA
	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	11	25	mA	
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	3	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	14	35	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	3	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	4	35	mA
Н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	2.5	20	mA
√ _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
l _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	50	-	V/µs



junction temperature

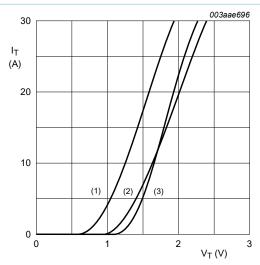


003aae699 2.0 I_{H} I_{H(25°C)} 1.5 1.0 0.5 - 60 - 10 40 140 T_j (°C)

Fig. 7. Normalized gate trigger current as a function of

junction temperature

Fig. 9. Normalized holding current as a function of junction temperature



 $V_o = 1.264 \text{ V}$ $R_s = 0.038 \Omega$

(1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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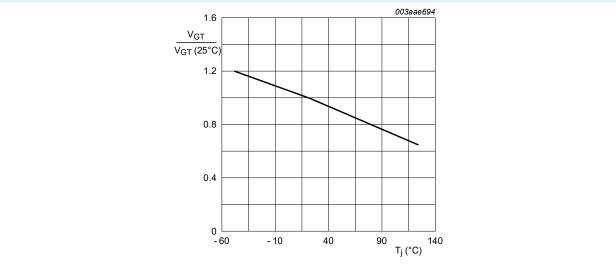
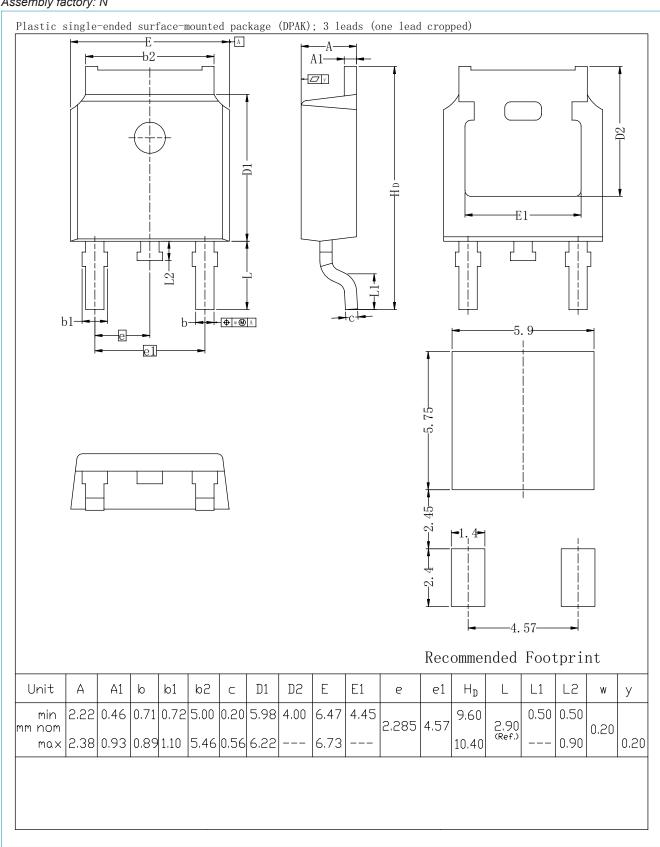


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

Assembly factory: N

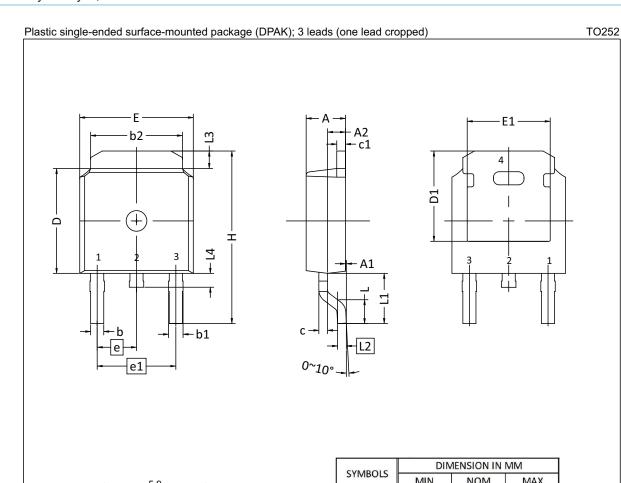


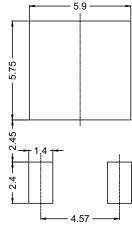
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Assembly factory: Q





Recommended Footprint

SYMBOLS	DIN	DIMENSION IN MM				
STIVIBULS	MIN	NOM	MAX			
Α	2.184	2.286	2.400			
A1	0.000		0.200			
A2	0.889	1.041	1.170			
b	0.635	0.762	0.889			
b1	0.680	0.840	1.143			
b2	4.953	5.340	5.500			
С	0.450	0.508	0.610			
c1	0.450	0.508	0.630			
D en entre	5.969	6.096	6.223			
D1	5.210	5.249	5.380			
E	6.350	6.604	6.800			
E1	4.318	4.826	4.920			
е		2.286BSC				
e1		4.572BSC				
Н	9.398	10.033	10.500			
L	1.270	1.520	2.032			
L1		2.921REF				
L2	0.408	0.508	0.608			
L3	0.889	1.016	1.270			
L4	0.600		1.016			

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.ween-semi.com
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